



## Description

The AO4437 uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

## General Features

$V_{DS} = -20V$   $I_D = -20A$

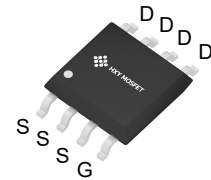
$R_{DS(ON)} < 19m\Omega @ V_{GS}=10V$

## Application

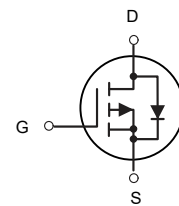
Battery protection

Load switch

Uninterruptible power supply



SOP-8



P-Channel MOSFET

## Package Marking and Ordering Information

| Product ID | Pack  | Brand      | Qty(PCS) |
|------------|-------|------------|----------|
| AO4437     | SOP-8 | HXY MOSFET | 3000     |

## Absolute Maximum Ratings( $T_c=25^{\circ}C$ unless otherwise noted)

| Symbol                  | Parameter                                                 | Rating     | Units         |
|-------------------------|-----------------------------------------------------------|------------|---------------|
| $V_{DS}$                | Drain-Source Voltage                                      | -20        | V             |
| $V_{GS}$                | Gate-Source Voltage                                       | +12        | V             |
| $I_D @ T_A=25^{\circ}C$ | Drain Current <sup>3</sup> , $V_{GS} @ 10V$               | -20        | A             |
| $I_D @ T_A=70^{\circ}C$ | Drain Current <sup>3</sup> , $V_{GS} @ 10V$               | -16        | A             |
| $I_{DM}$                | Pulsed Drain Current <sup>1</sup>                         | -68        | A             |
| $P_D @ T_A=25^{\circ}C$ | Total Power Dissipation                                   | 18         | W             |
| $T_{STG}$               | Storage Temperature Range                                 | -55 to 150 | $^{\circ}C$   |
| $T_J$                   | Operating Junction Temperature Range                      | -55 to 150 | $^{\circ}C$   |
| $R_{thj-a}$             | Maximum Thermal Resistance, Junction-ambient <sup>3</sup> | 75         | $^{\circ}C/W$ |



### Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)

| Symbol                       | Parameter                                      | Conditions                                                       | Min. | Typ.   | Max.      | Unit                |
|------------------------------|------------------------------------------------|------------------------------------------------------------------|------|--------|-----------|---------------------|
| $BV_{DSS}$                   | Drain-Source Breakdown Voltage                 | $V_{GS}=0V$ , $I_D=-250\mu A$                                    | -20  | ---    | ---       | V                   |
| $\Delta BV_{DSS}/\Delta T_J$ | $BV_{DSS}$ Temperature Coefficient             | Reference to $25^\circ\text{C}$ , $I_D=-1\text{mA}$              | ---  | -0.012 | ---       | $V/^\circ\text{C}$  |
| $R_{DS(ON)}$                 | Static Drain-Source On-Resistance <sup>2</sup> | $V_{GS}=-4.5V$ , $I_D=-10A$                                      | ---  | 15     | 19        | $m\Omega$           |
|                              |                                                | $V_{GS}=-2.5V$ , $I_D=-8A$                                       | ---  | 19     | 23        |                     |
| $V_{GS(th)}$                 | Gate Threshold Voltage                         | $V_{GS}=V_{DS}$ , $I_D=-250\mu A$                                | -0.4 | -0.7   | -1.0      | V                   |
| $\Delta V_{GS(th)}$          | $V_{GS(th)}$ Temperature Coefficient           |                                                                  | ---  | 2.94   | ---       | $mV/^\circ\text{C}$ |
| $I_{DSS}$                    | Drain-Source Leakage Current                   | $V_{DS}=-15V$ , $V_{GS}=0V$ , $T_J=25^\circ\text{C}$             | ---  | ---    | 1         | $\mu A$             |
| $I_{GSS}$                    | Gate-Source Leakage Current                    | $V_{GS}=\pm 12V$ , $V_{DS}=0V$                                   | ---  | ---    | $\pm 100$ | nA                  |
| $g_{fs}$                     | Forward Transconductance                       | $V_{DS}=-5V$ , $I_D=-10A$                                        | ---  | 43     | ---       | S                   |
| $Q_g$                        | Total Gate Charge (-4.5V)                      | $V_{DS}=-10V$ , $V_{GS}=-4.5V$ , $I_D=-10A$                      | ---  | 35     | ---       | nC                  |
| $Q_{gs}$                     | Gate-Source Charge                             |                                                                  | ---  | 5.0    | ---       |                     |
| $Q_{gd}$                     | Gate-Drain Charge                              |                                                                  | ---  | 10     | ---       |                     |
| $T_{d(on)}$                  | Turn-On Delay Time                             | $V_{DD}=-10V$ , $V_{GS}=-4.5V$ ,<br>$R_G=3.3\Omega$ , $I_D=-10A$ | ---  | 12.0   | ---       | ns                  |
| $T_r$                        | Rise Time                                      |                                                                  | ---  | 40.0   | ---       |                     |
| $T_{d(off)}$                 | Turn-Off Delay Time                            |                                                                  | ---  | 30     | ---       |                     |
| $T_f$                        | Fall Time                                      |                                                                  | ---  | 10     | ---       |                     |
| $C_{iss}$                    | Input Capacitance                              | $V_{DS}=-15V$ , $V_{GS}=0V$ , $f=1\text{MHz}$                    | ---  | 2800   | ---       | pF                  |
| $C_{oss}$                    | Output Capacitance                             |                                                                  | ---  | 690    | ---       |                     |
| $C_{rss}$                    | Reverse Transfer Capacitance                   |                                                                  | ---  | 590    | ---       |                     |

### Diode Characteristics

| Symbol   | Parameter                                | Conditions                                                  | Min. | Typ. | Max.  | Unit |
|----------|------------------------------------------|-------------------------------------------------------------|------|------|-------|------|
| $I_S$    | Continuous Source Current <sup>1,4</sup> | $V_G=V_D=0V$ , Force Current                                | ---  | ---  | -20.0 | A    |
| $I_{SM}$ | Pulsed Source Current <sup>2,4</sup>     |                                                             | ---  | ---  | ---   | A    |
| $V_{SD}$ | Diode Forward Voltage <sup>2</sup>       | $V_{GS}=0V$ , $I_S=-1A$ , $T_J=25^\circ\text{C}$            | ---  | ---  | -1.2  | V    |
| $t_{rr}$ | Reverse Recovery Time                    | $I_F=-10A$ , $dI/dt=100A/\mu s$ ,<br>$T_J=25^\circ\text{C}$ | ---  | 27   | ---   | nS   |
| $Q_{rr}$ | Reverse Recovery Charge                  |                                                             | ---  | 17.8 | ---   | nC   |

Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu s$  , duty cycle  $\leq 2\%$
- 3.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 4.The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.



## Typical Characteristics

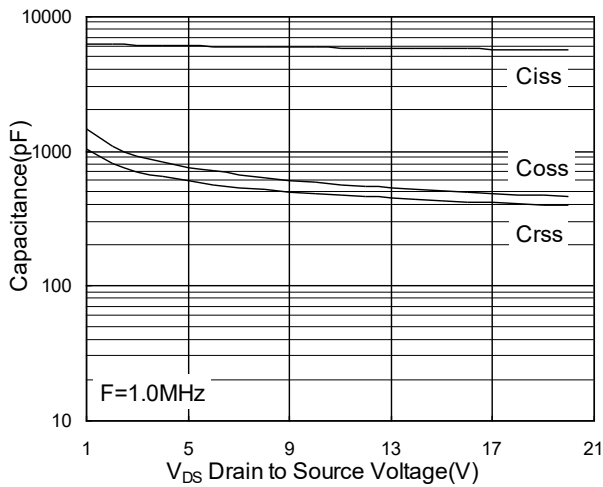


Fig.7 Capacitance

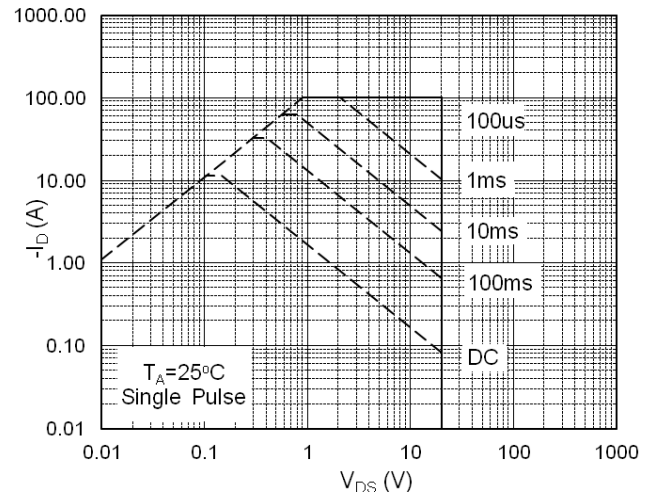


Fig.8 Safe Operating Area

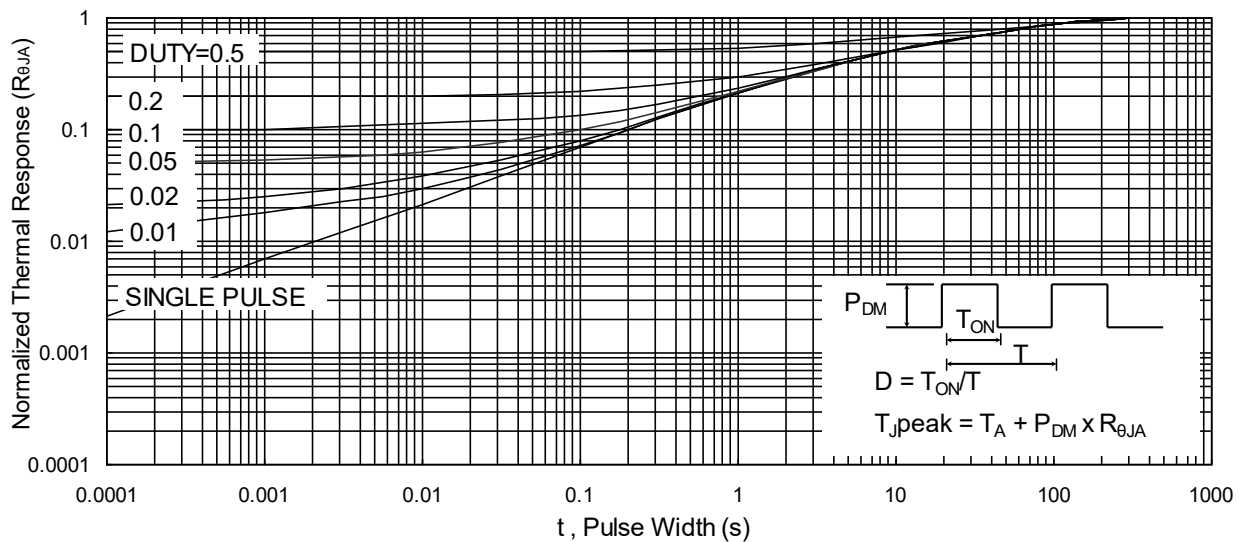


Fig.9 Normalized Maximum Transient Thermal Impedance

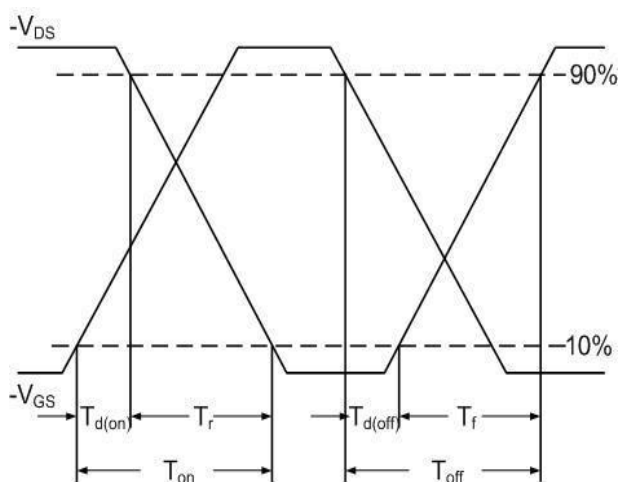


Fig.10 Switching Time Waveform

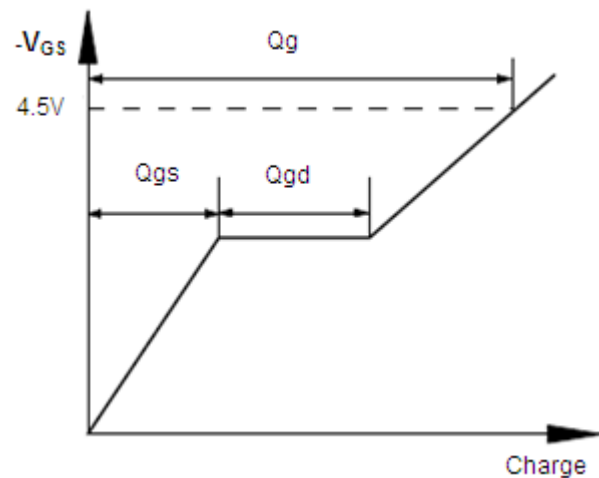
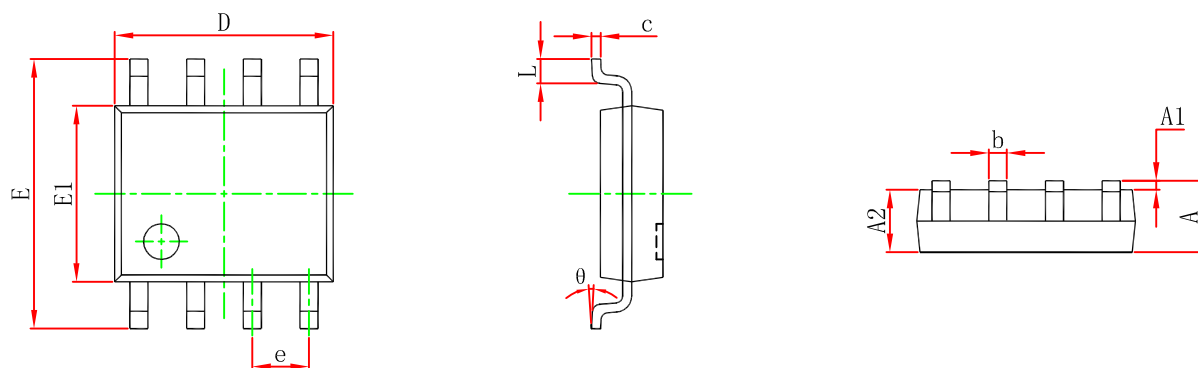


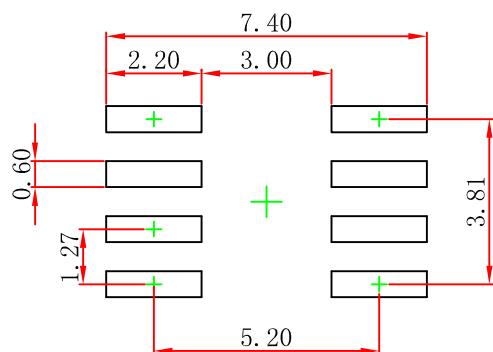
Fig.11 Gate Charge Waveform



## SOP-8 Package Outline Dimensions



| Symbol | Dimensions In Millimeters |       | Dimensions In Inches |       |
|--------|---------------------------|-------|----------------------|-------|
|        | Min                       | Max   | Min                  | Max   |
| A      | 1.350                     | 1.750 | 0.053                | 0.069 |
| A1     | 0.100                     | 0.250 | 0.004                | 0.010 |
| A2     | 1.350                     | 1.550 | 0.053                | 0.061 |
| b      | 0.330                     | 0.510 | 0.013                | 0.020 |
| c      | 0.170                     | 0.250 | 0.007                | 0.010 |
| D      | 4.800                     | 5.000 | 0.189                | 0.197 |
| e      | 1.270 (BSC)               |       | 0.050 (BSC)          |       |
| E      | 5.800                     | 6.200 | 0.228                | 0.244 |
| E1     | 3.800                     | 4.000 | 0.150                | 0.157 |
| L      | 0.400                     | 1.270 | 0.016                | 0.050 |
| θ      | 0°                        | 8°    | 0°                   | 8°    |



### Note:

1. Controlling dimension; in millimeters.
2. General tolerance:  $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.



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